

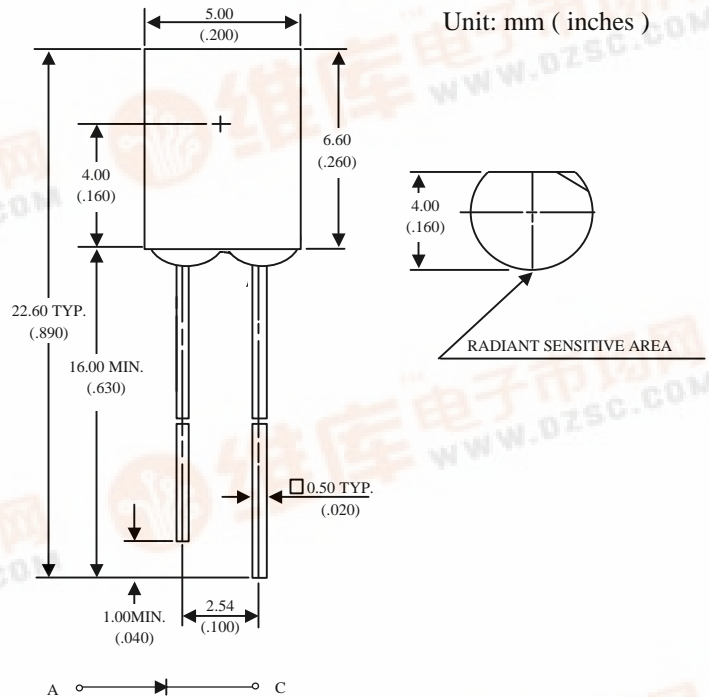
SIDE LOOK PACKAGE PIN PHOTODIODE

MID-85H1C

Description

The MID-85H1C is a photodiode mounted in special dark plastic package and suitable for the IRED (850nm/880nm) Type.

Package Dimensions



Features

- High photo sensitivity
- Low junction capacitance
- High cut -off frequency
- Fast switching time
- Suitable for the IRED 850nm/880nm type

Notes :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 1.0 mm (.040") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Operating Temperature Range	-55°C to $+100^\circ\text{C}$	
Storage Temperature Range	-55°C to $+100^\circ\text{C}$	
Lead Soldering Temperature	260°C for 5 seconds	

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Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse Break Down Voltage	I _R =0.1mA Ee=0	V _{(BR)R}	30			V
Reverse Dark Current	V _R =10V Ee=0	I _D			30	nA
Open Circuit Voltage	λ=850nm Ee=0.1mW/cm ²	V _{OC}		350		mV
Rise Time	V _R =10V λ=850nm	Tr		50		nsec
Fall Time	R _L =50Ω	Tf		50		
Light Current	V _R =5V, λ=850nm Ee=0.1mW/cm ²	I _L		9		μA
Total Capacitance	V _R =3V, f=1MHz Ee=0	C _T		25		pF

Typical Optical-Electrical Characteristic Curves

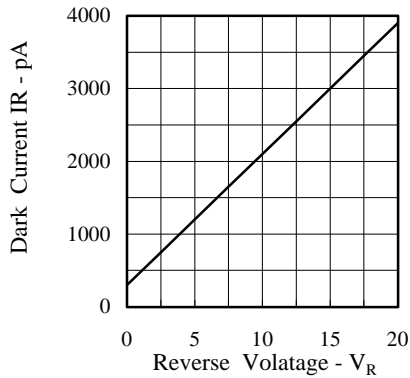


FIG.1 DARK CURRENT VS REVERSE VOLTAGE
TEMP=25°C, Ee=0 mW/cm²

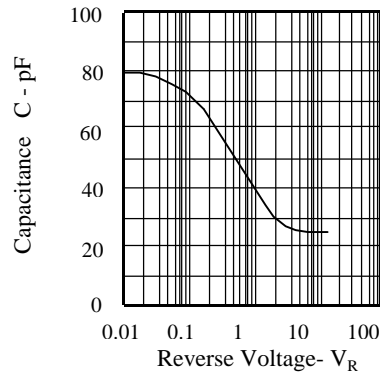


FIG.2 CAPACITANCE VS. REVERSE VOLTAGE
F=1MHz ; Ee=0mW/cm²

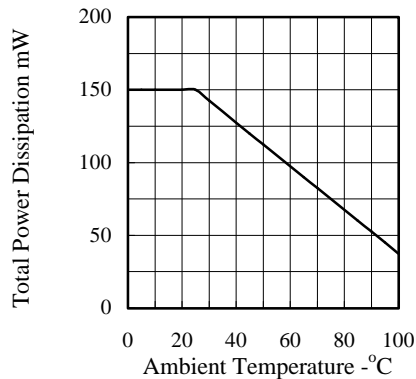


FIG.3 TOTAL POWER DISSIPATION
VS. AMBIENT TEMPERATURE

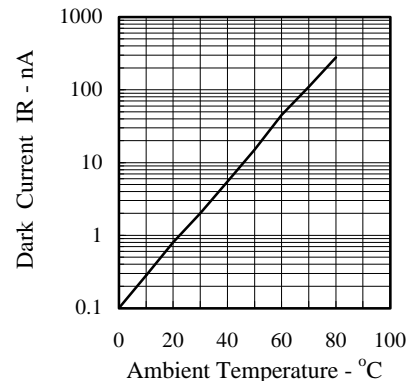


FIG.4 DARK CURRENT VS AMBIENT TEMPERATURE
V_R=10V, Ee=0 mW/cm²

Typical Optical-Electrical Characteristic Curves

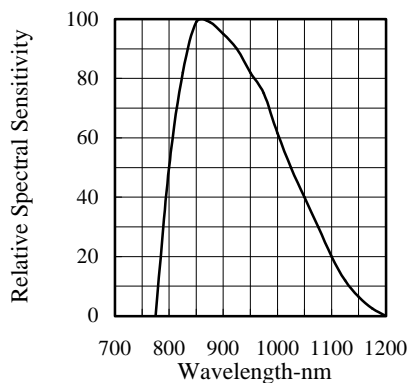


FIG.5 RELATIVE SPECTRAL SENSITIVITY VS. WAVELENGTH

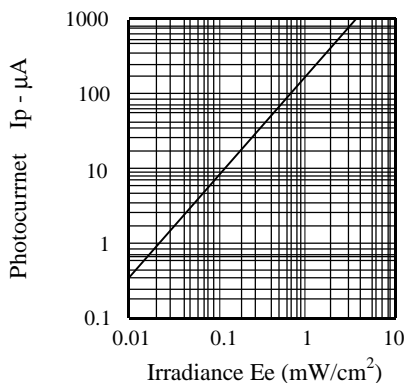


FIG.6 PHOTOCURRENT VS. IRRADIANCE = 850 nm

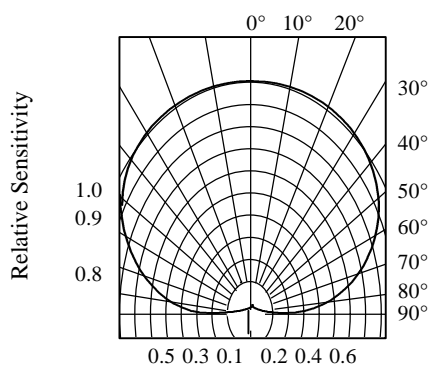


FIG.7 SENSITIVITY DIAGRAM